

Application No.: 10/686,893 YAO-3990US3  
Amendment Dated: February 27, 2007  
Reply to Office Action of: October 27, 2006



**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Appln. No: 10/686,893  
Applicants: Hidetoshi ISHIDA, et al.  
Filed: October 16, 2003  
Title: ETCHANT AND METHOD FOR FABRICATING A SEMICONDUCTOR DEVICE USING THE SAME  
TC/A.U.: 2823  
Examiner: Q. Jefferson  
Confirmation No.: 8582  
Docket No.: YAO-3990US3

*DO NOT ENTER  
3/12/07 QVJ*

**AMENDMENT UNDER 37 C.F.R. § 1.116**

**Expedited Procedure**

**Mail Stop AF**  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Responsive to the Final Office Action dated **October 27, 2006**, please amend the above-identified application as follows:

- Amendments to the Specification** begin on page \_\_\_\_\_ of this paper.
- Amendments to the Claims** are reflected in the listing of claims which begins on page 2 of this paper.
- Amendments to the Drawings** begin on page \_\_\_\_\_ of this paper and include an attached replacement sheet(s).
- Amendments to the Abstract** are on page \_\_\_\_\_ of this paper. A clean version of the Abstract is on page \_\_\_\_\_ of this paper.
- Remarks/Arguments** begin on page 3 of this paper.